

General Description

The CMSA020N45 uses advanced technology to provide excellent RDS (ON) . This device is suitable to be used as the low side FET general purpose.

Features

- RDS(ON)<1.7mΩ @ VGS=10V
- 100% avalanche tested
- RoHS and Halogen-Free Compliant
- High Current Capability

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	45	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	100	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	80	A
I_{DM}	Pulsed Drain Current	300	A
EAS	Single Pulse Avalanche Energy	420	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	75	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	---	45	°C/W
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	2.0	°C/W

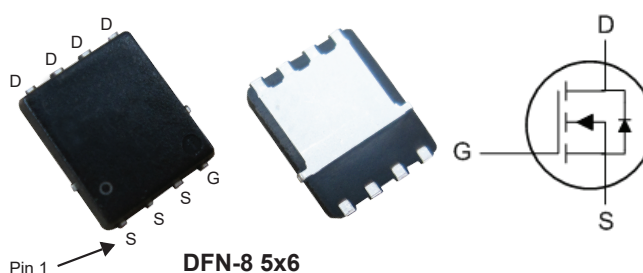
Product Summary

BVDSS	RDS(ON)	ID
45V	1.7mΩ	100A

Applications

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA020N45	DFN-8 5*6	CMSA020N45

N-Channel Enhancement Mode Field Effect Transistor

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	45	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=28A$	---	---	1.7	m Ω
		$V_{GS}=4.5V$, $I_D=28A$	---	---	2.0	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	2.3	---	Ω
Q_g	Total Gate Charge	$V_{DS}=32V$, $I_D=20A$ $V_{GS}=10V$	---	60	---	nC
Q_{gs}	Gate-Source Charge		---	14	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V$, $V_{GS}=10V$, $I_D=20A$ $R_{GEN}=2.5\Omega$	---	15	---	ns
T_r	Rise Time		---	46	---	
$T_{d(off)}$	Turn-Off Delay Time		---	36	---	
T_f	Fall Time		---	8	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	6800	---	pF
C_{oss}	Output Capacitance		---	1000	---	
C_{rss}	Reverse Transfer Capacitance		---	1100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	100	A
$I_{S,pulse}$	Diode pulse current		---	---	300	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=28A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

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